

## 2n2322 to 2n2326

### SILICON THYRISTORS

All-diffused PNP thyristors designed for grating operation in mA/ $\mu$ A signal or detection circuits  
Compliance to RoHS.

#### MAXIMUM RATINGS (\*)

$T_J=125^{\circ}\text{C}$  unless otherwise noted,  $R_{GK}=1000\Omega$

Symbol	Ratings	2N2322	2N2323	2N2324	2N2325	2N2326	Unit
$V_{RRM(REP)}$	Peak reverse blocking voltage (*)	25	50	100	150	200	V
$V_{RSM(NON-REP)}$	Non-repetitive peak blocking reverse voltage ( $t<5.0$ ms)	40	75	150	225	300	V
$I_{T(RMS)}$	Forward Current RMS (all conduction angles)	1.6					A
$I_{TSM}$	Peak Surge Current (One-Half Cycle, 60Hz) No Repetition Until Thermal Equilibrium is Restored.	15					A
$P_{GM}$	Peak Gate Power – Forward	0.1					W
$P_{G(AV)}$	Average Gate Power - Forward	0.01					W
$I_{GM}$	Peak Gate Current – Forward	0.1					A
$V_{GFM}$	Peak Gate Voltage - Forward	6.0					V
$V_{GRM}$	Peak Gate Voltage - Reverse	6.0					V
$T_J$	Operating Junction Temperature Range	-65 to +125					°C
$T_{STG}$	Storage Temperature Range	-65 to +150					

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### ELECTRICAL CHARACTERISTICS (\*)

T<sub>J</sub>=25°C unless otherwise noted, R<sub>GK</sub>=1000Ω

Symbol	Ratings	2N2322	2N2323	2N2324	2N2325	2N2326	Unit
V <sub>DRM</sub>	Peak Forward Blocking Voltage (1) <b>Min :</b>	25	50	100	150	200	V
I <sub>RRM</sub>	Peak Reverse Blocking Current (Rated V <sub>DRM</sub> , T <sub>J</sub> =125°C)	Max : 100					μA
I <sub>DRM</sub>	Peak Forward Blocking Current (Rated V <sub>DRM</sub> , T <sub>J</sub> =125°C)	Max : 100					μA
V <sub>TM</sub>	Forward « on » Voltage I <sub>TM</sub> =1.0 A Peak	Max : 1.5					V
	I <sub>TM</sub> =3.14 A Peak T <sub>C</sub> =85°C	Max : 2.0					
I <sub>GT</sub>	Gate Trigger Current (2) Anode Voltage=6.0 Vdc R <sub>L</sub> =100Ω	Max : 200					μA
	Anode Voltage=6.0 Vdc R <sub>L</sub> =100Ω, T <sub>C</sub> =-65°C	Max : 350					
V <sub>GT</sub>	Gate Trigger Voltage Anode Voltage=6.0 V R <sub>L</sub> =100Ω	Max : 0.8					V
	Anode Voltage=6.0 V R <sub>L</sub> =100Ω, T <sub>C</sub> =-65°C	Max : 1.0					
	V <sub>DRM</sub> = Rated R <sub>L</sub> =100Ω, T <sub>J</sub> =125°C	Min : 0.1					
I <sub>H</sub>	Holding Current Anode Voltage=6.0 V	Max : 2.0					mA
	Anode Voltage=6.0 V T <sub>C</sub> =-65°C	Max : 3.0					
	Anode Voltage=6.0 V T <sub>C</sub> =125°C	Min : 0.15					

(\*) JEDEC Registered Values

(1) V<sub>RSM</sub> and V<sub>DRM</sub> can be applied for all types on a continuous dc basis without incurring damage.

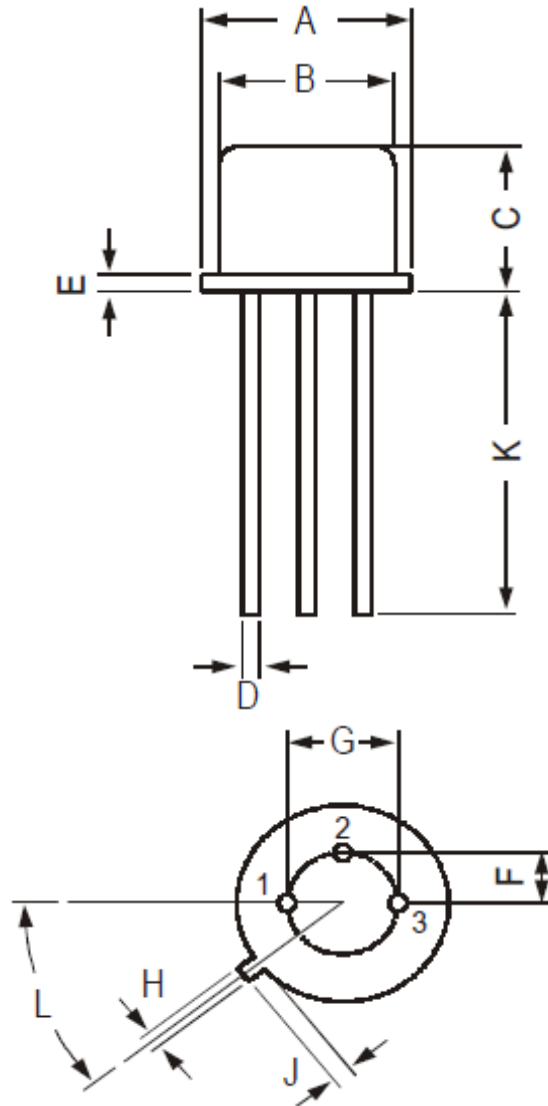
(2) R<sub>GK</sub> current is not included in measurement.

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### MECHANICAL DATA CASE TO-39

DIMENSIONS (mm)		
	min	max
A	8.50	9.39
B	7.74	8.50
C	6.09	6.60
D	0.40	0.53
E	-	0.88
F	2.41	2.66
G	4.82	5.33
H	0.71	0.86
J	0.73	1.02
K	12.70	-
L	42°	48°

Pin 1 :	kathode
Pin 2 :	Gate
Pin 3 :	Anode
Case :	anode



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